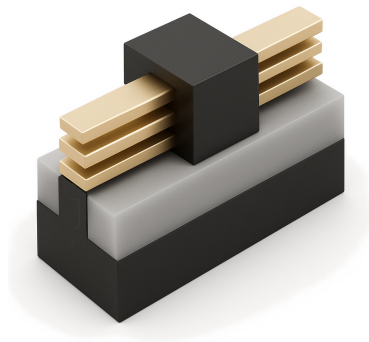
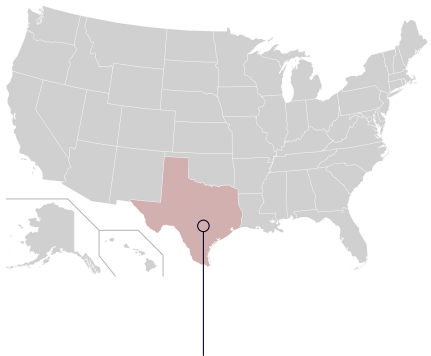


High-throughput computing, cloud cyberinfrastructure, and machine learning for semiconductor design

Feliciano Giustino

Oden Institute & Department of Physics
University of Texas at Austin

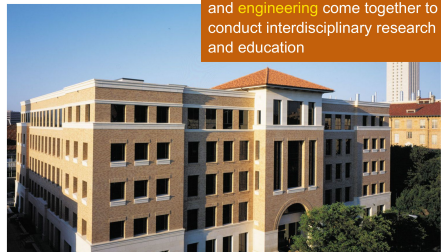




University of Texas at Austin



A research community where computing, mathematics, science and engineering come together to conduct interdisciplinary research and education



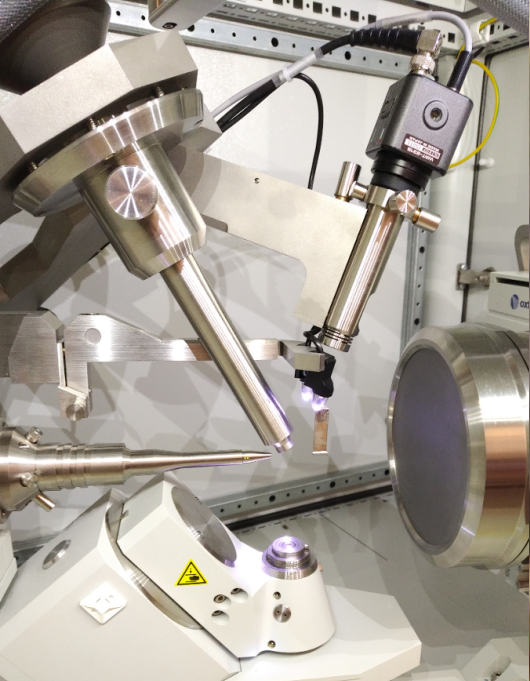
quantum dot molecule

eliashberg_cont_raxis.f90
eliashberg_aniso_jaxis.f90
eliashberg_iso_cont_raxis.f90
eliashberg_iso_jaxis.f90
eliashberg_iso_raxis.f90
eliashberg_pp.f90
eliashberg_readfiles.f90
eliashberg_setup.f90
eliashberg_write.f90
eliashberg.f90
eliashbergcom.f90
elph2.f90
elphel2_shuffle.f90
elphon_shuffle_wrap.f90
elphon_shuffle.f90
ephbloch2wane.f90
ephbloch2wanp.f90
ephwan2bloch_mem.f90
ephwan2bloch.f90
ephwan2blochp_mem.f90
ephwan2blochp.f90
ephwann_shuffle_mem.f90
ephwann_shuffle.f90
epw_init.f90
epw_readin.f90
epw_setup.f90
epw_summary.f90
epw.f90
epw.x
epwcom.f90
fermiwindow.f90
gen_freqgrid.f90
gmap_sym.f90
hambloch2wan.f90
hamwan2bloch.f90
io_dyn_mat2.f90
io_epw.f90
io_scattering.f90

OUTLINE

```
63 #if defined(_MPI)
64 INTEGER(kind=MPI_OFFSET_KIND) :: lrepmatw
65 !! Offset to tell where to start reading the file
66 INTEGER(kind=MPI_OFFSET_KIND) :: lrepmatw2
67 !! Offset to tell where to start reading the file
68 #else
69 INTEGER(kind=8) :: lrepmatw
70 !! Offset to tell where to start reading the file
71 INTEGER(kind=8) :: lrepmatw2
72 !! Offset to tell where to start reading the file
73 #endif
74 !
75 REAL(kind=DP) :: rdotk
76 !! Exponential for the dot product
77 !
78 COMPLEX(kind=DP) :: rdotk
79 !! Temporary matrix for the dot product
80 COMPLEX(kind=DP) :: rdotk
81 !! Factor for the dot product
82 COMPLEX(kind=DP) :: rdotk
83 !! EL-ph matrix element
84 !
85 CALL start_clock('epw')
86 !-----
87 ! STEP 3: inverse Fourier transform
88 !-----
89 !
90 !  $g_{\sim}(k') = \sum_R 1/n_{deg}$ 
91 !
92 !  $g_{\sim}(k')$  is epmatf (nmodes,
93 ! every pool works with its own
94 !
95 IF (parallel_k) THEN
96   CALL para_bounds(ir_start, ir_end, n_k)
97 ELSEIF (parallel_q) THEN
98   ir_start = 1
```

high-performance
computing



computational
materials discovery

Yesterday

Neural network potentials
for phonons



Jaesuk Park

Symbolic regression
for electrons



Nick Pant

2D Materials



Viet-Anh Ha

GPU acceleration



Tae Yun Kim

EPWpy and CSSI



Sabyasachi Tiwari

How much energy does it take to train LLMs

CO2 Equivalent Emissions (Tonnes) by Selected Machine Learning Models and Real Life Examples, 2022

Source: Luccioni et al., 2022; Strubell et al., 2019 | Chart: 2023 AI Index Report

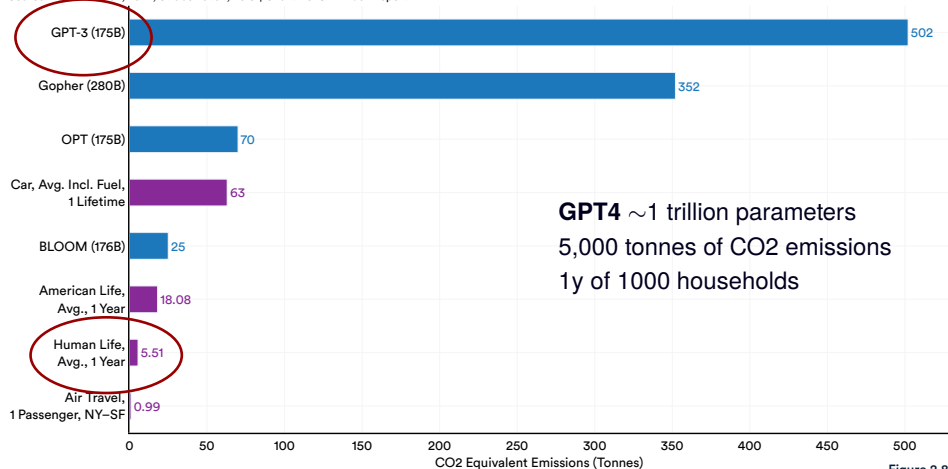
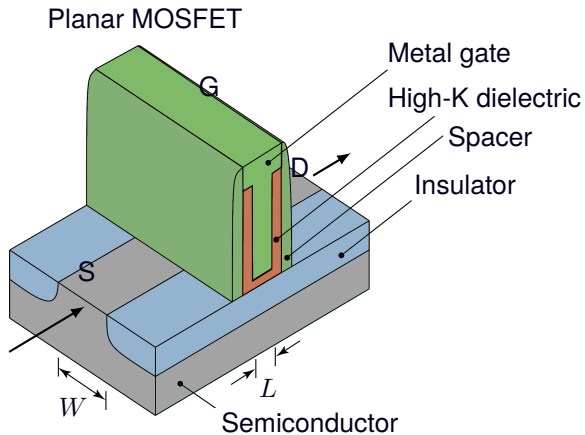
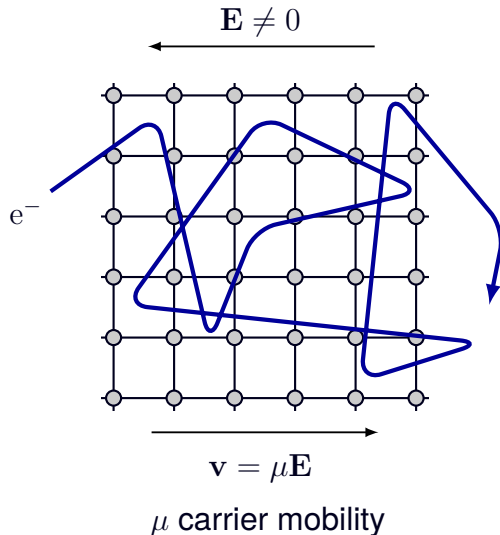
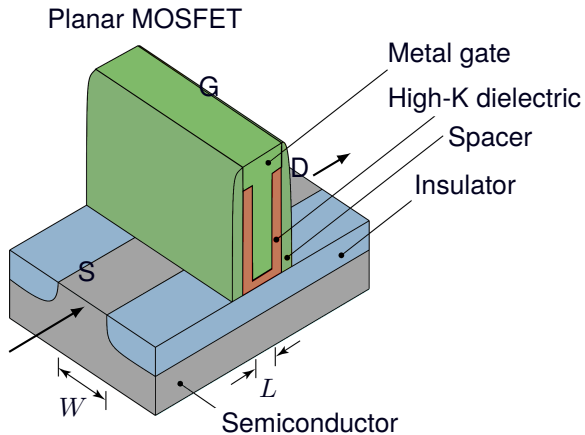


Figure 2.8.2

Field effect transistor

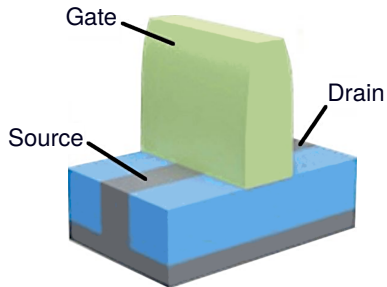


Field effect transistor



Evolution of FET layout

Planar FET

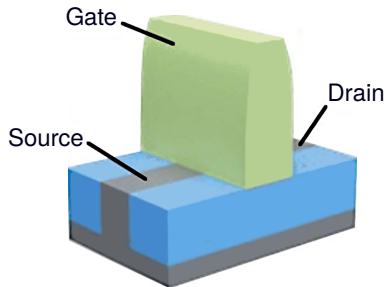


1971

Intel 4004 chip
10 μ m process
2,300 transistors

Evolution of FET layout

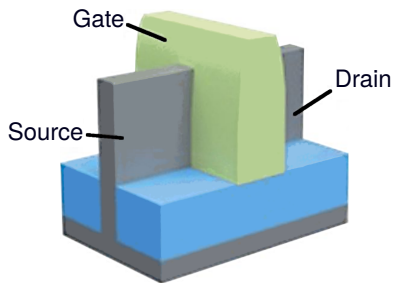
Planar FET



1971

Intel 4004 chip
10 μ m process
2,300 transistors

FinFET

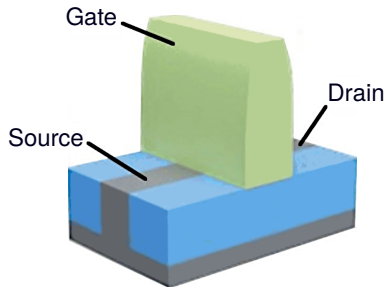


2012

Intel Ivy Bridge chip
22nm process
1.4 billion transistors

Evolution of FET layout

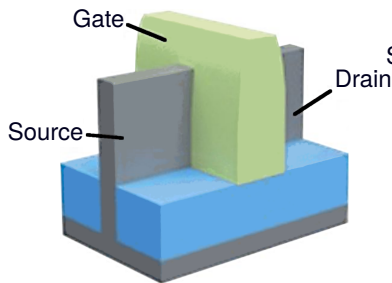
Planar FET



1971

Intel 4004 chip
10 μ m process
2,300 transistors

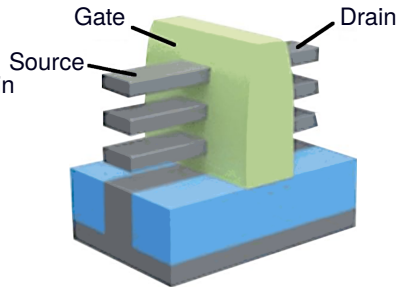
FinFET



2012

Intel Ivy Bridge chip
22nm process
1.4 billion transistors

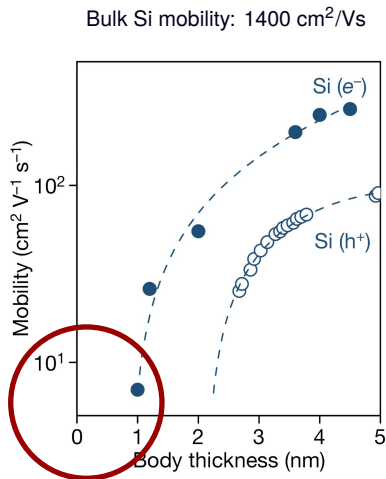
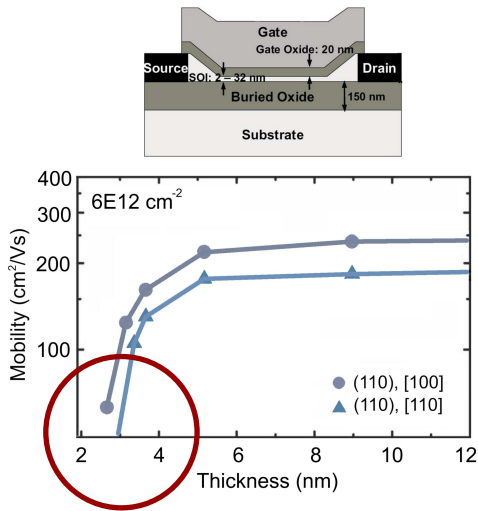
GAAFET or RibbonFET



2022

Apple A16 Bionic chip
TSMC 4nm process
16 billion transistors

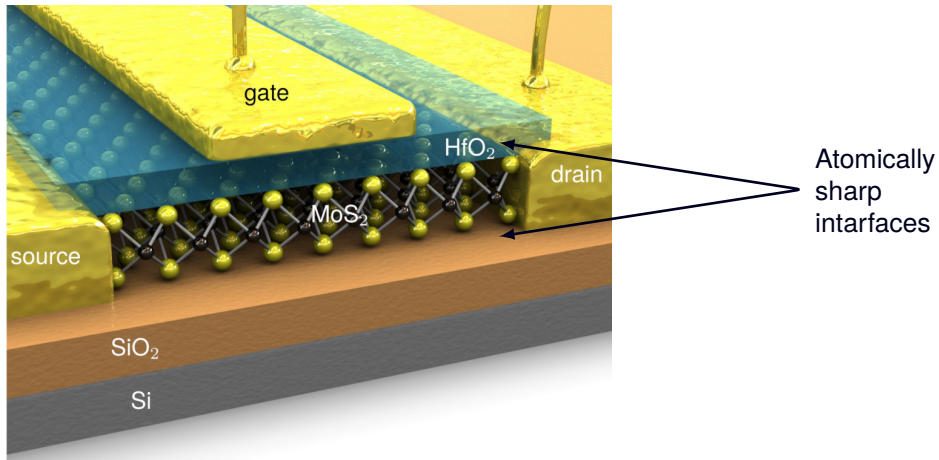
Degradation of carrier mobility in ultrathin silicon



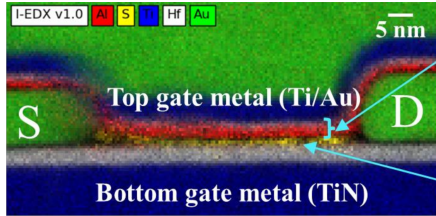
Left figures from: Tsutsui Hiramoto, IEEE Trans. Electron Devices 53, 2582 (2006)

Right figure from: Liu et al, Nature 591, 43 (2021)

The promise of 2D semiconductors



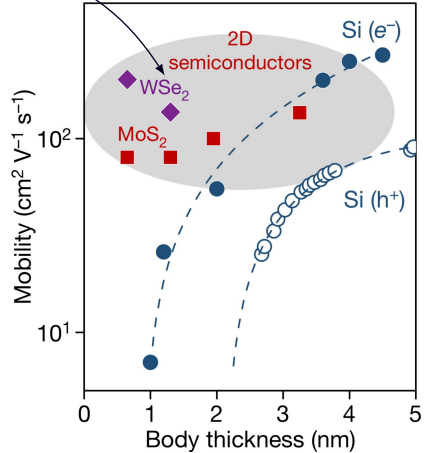
Current limitations of 2DFETs



top gate oxide
Al₂O₃/HfO₂ bilayer

0.7 nm
monolayer MoS₂

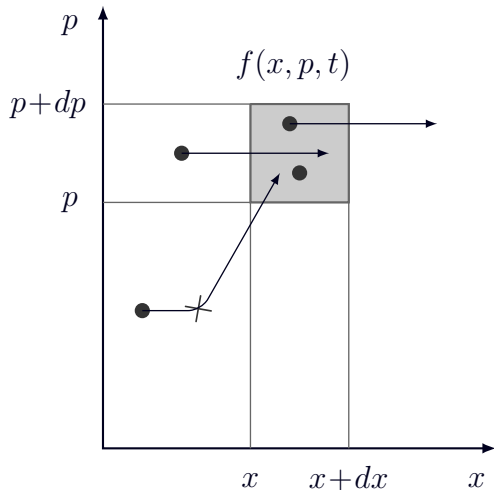
mobility ~ 100 cm²/Vs



Left figure from: Dorow et al., IEDM 2022, doi: 10.1109/IEDM45625.2022.10019524

Right figure from: Liu et al, Nature 591, 43 (2021)

Ab initio Boltzmann transport equation



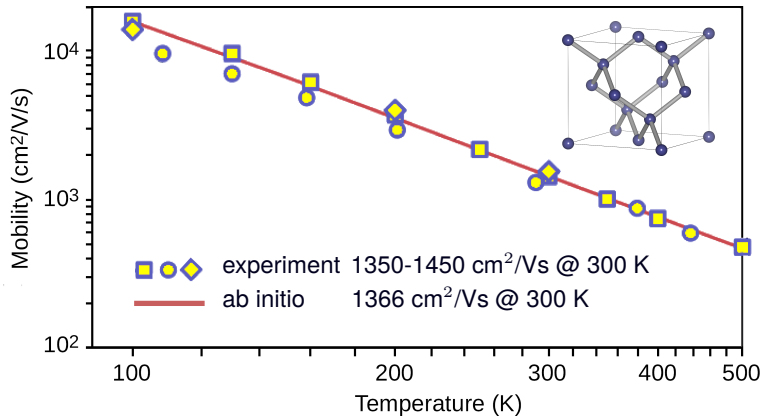
Collisionless flow

Scattering

$$\frac{\partial f}{\partial t} + \frac{\partial f}{\partial \mathbf{r}} \cdot \frac{d\mathbf{r}}{dt} + \frac{\partial f}{\partial \mathbf{p}} \cdot \frac{d\mathbf{p}}{dt} = \Gamma_{\text{in}} - \Gamma_{\text{out}}$$

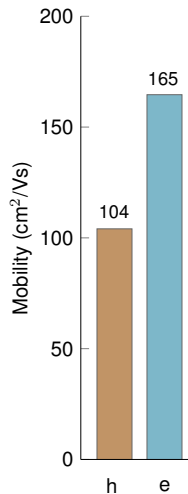
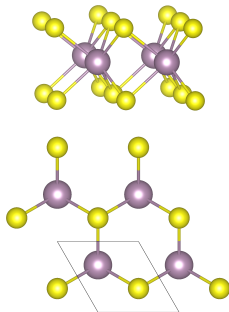
Comparison between theory and experiment

Example **silicon**



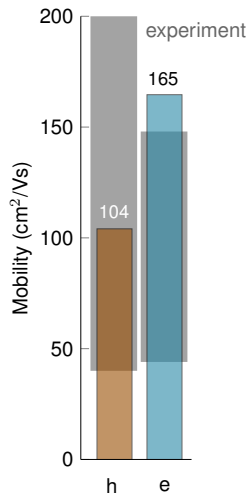
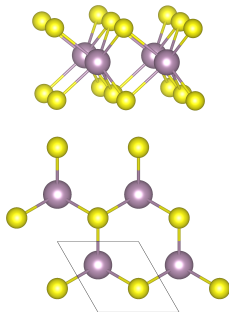
Theory vs. experiments for 2D materials

Example **MoS₂**



Theory vs. experiments for 2D materials

Example **MoS₂**

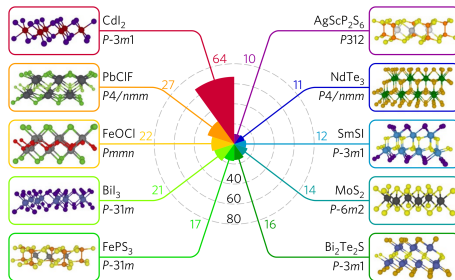
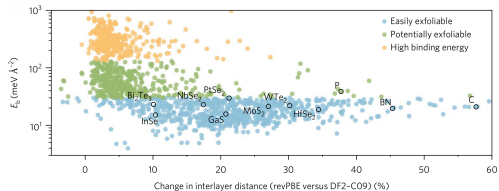


2D Materials Databases

Table 1 | Database statistics

	Unique to the ICSD	Unique to the COD	Common to both	Total sum
Experimental data				
CIF inputs	99,212	87,070		186,282
Unique 3D structures (set A)	34,548	60,354	13,521	108,423
Layered 3D structures (set B)	3,257	1,180	1,182	5,619
DFT calculations				
Layered 3D, relaxed (set C)	2,165	175	870	3,210
Binding energies (set D)	1,795	126	741	2,662
2D easily exfoliable (EE)	663	79	294	1,036
2D potentially exfoliable (PE)	524	34	231	789
Total	1,187	113	525	1,825

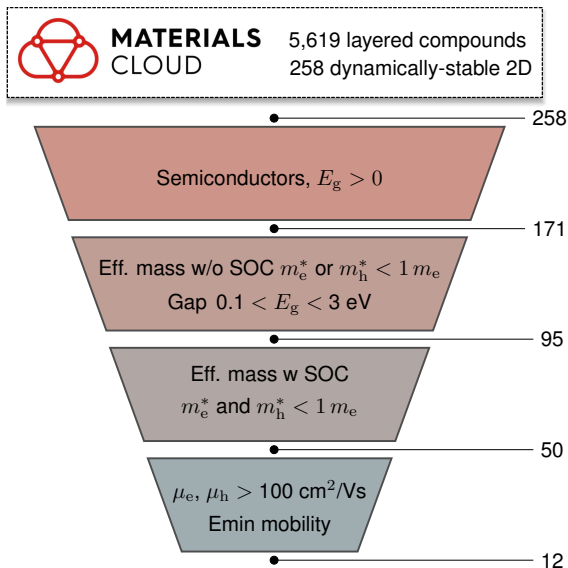
Experimental data: number of structures imported from the two databases (ICSD or COD, uniqueness not tested), number of unique 3D structures in each imported set or common to both (set A), and number of layered 3D structures identified using the geometrical criteria discussed in the text (set B). DFT calculations: number of structures that were relaxed (set C), number of structures that remain classified as layered after relaxation and for which binding energies were computed (set D), and number of easily or potentially (see text) exfoliable compounds.



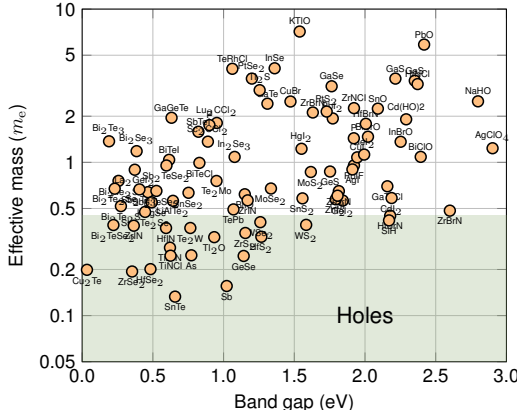
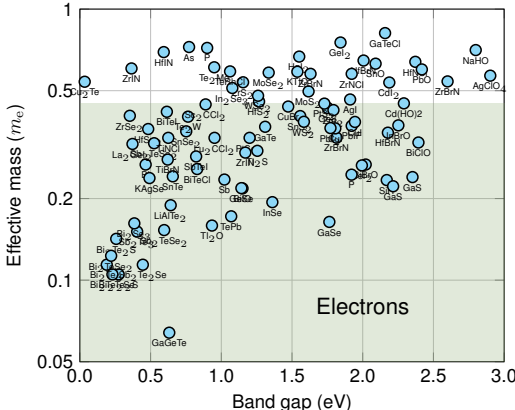
Figures from: *Materials Cloud 2D Database*, Mounet, Marzari, et al, Nat Nanotech 13, 246 (2018)

See also: *Computational 2D Materials Database*, Hastrup, Thygesen, et al, 2D Materials 5, 042002 (2018)

High-throughput screening workflow

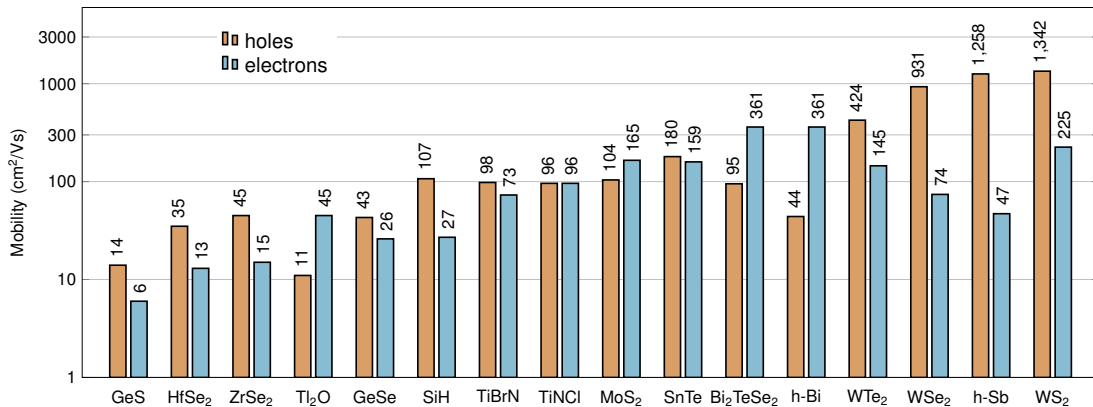


Pre-screening via effective masses

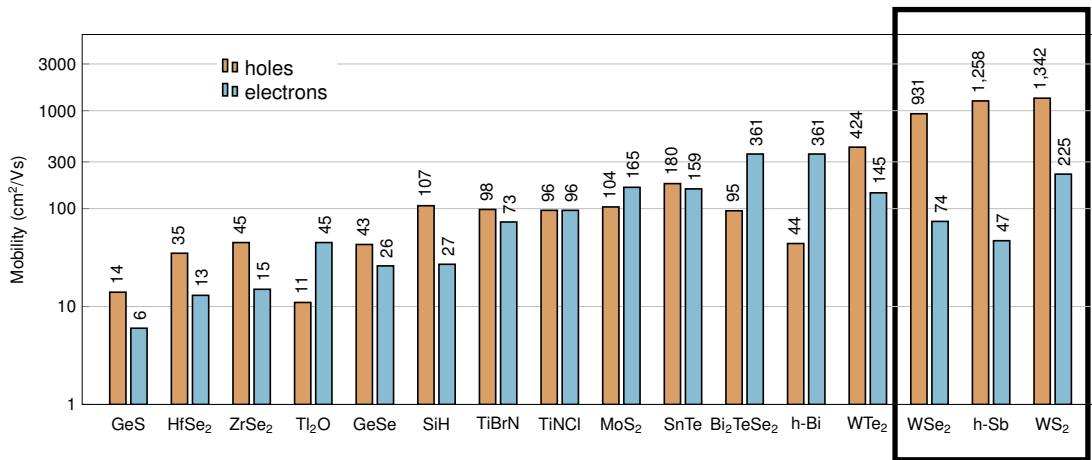


Set effective mass cutoff to $0.45 m_e$ based on $100 \text{ cm}^2/\text{Vs}$ mobility target

Top 2D semiconductors from *ab initio* BTE



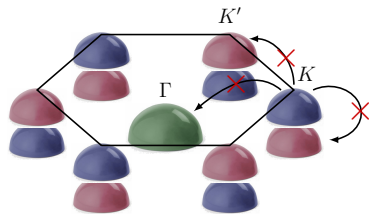
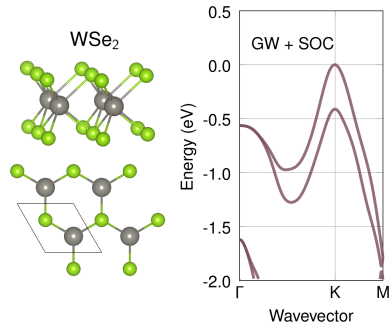
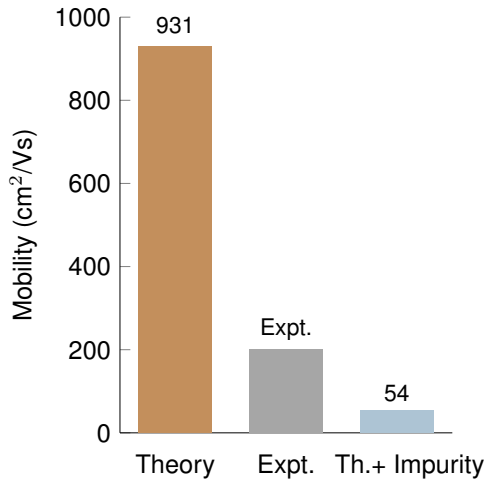
Top 2D semiconductors from *ab initio* BTE



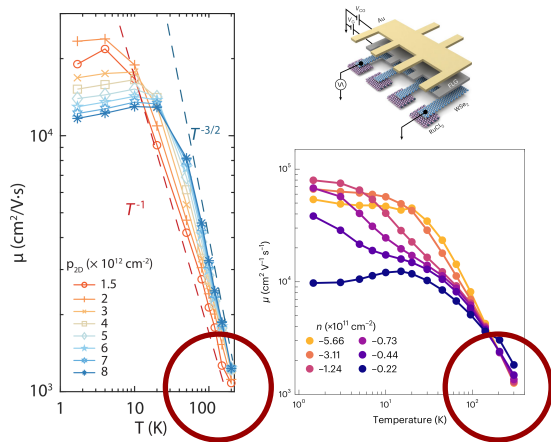
Ha & FG, npj Comput. Mater. 10, 229 (2024)

See also: Cheng et al, JACS 140, 17895 (2018); JACS 141, 16296 (2019); PRL 125, 177701 (2020)

Spin-valley locking in WSe₂ boosts mobility



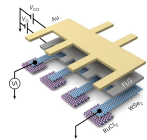
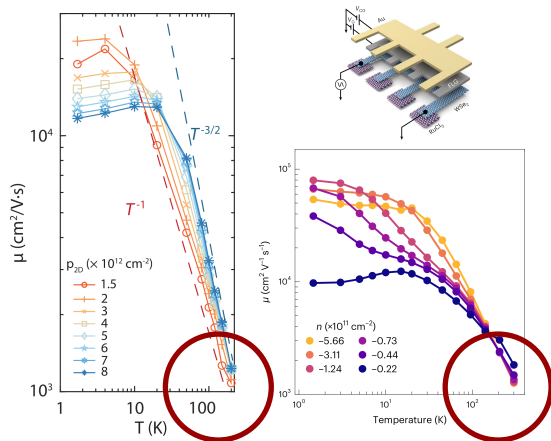
Recent measurements of high-quality WSe₂ samples



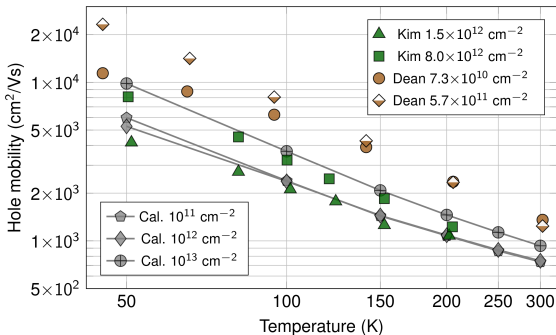
Left figures from: Joe, Kim, et al, Phys. Rev. Lett. 132, 056303 (2024)

Middle figures from: Pack, Dean, et al, Nat. Nanotechnol. 19, 948 (2024)

Recent measurements of high-quality WSe₂ samples



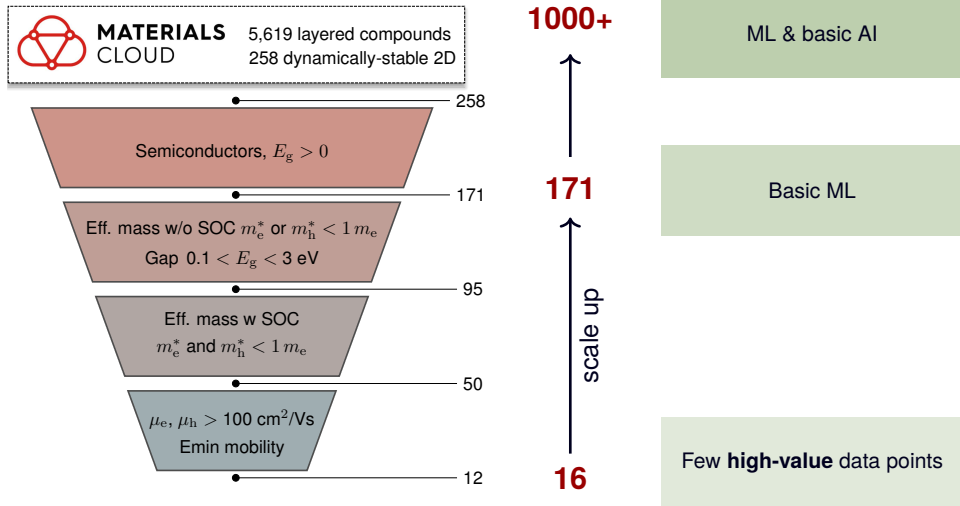
Successfully predicted by *aiBTE*



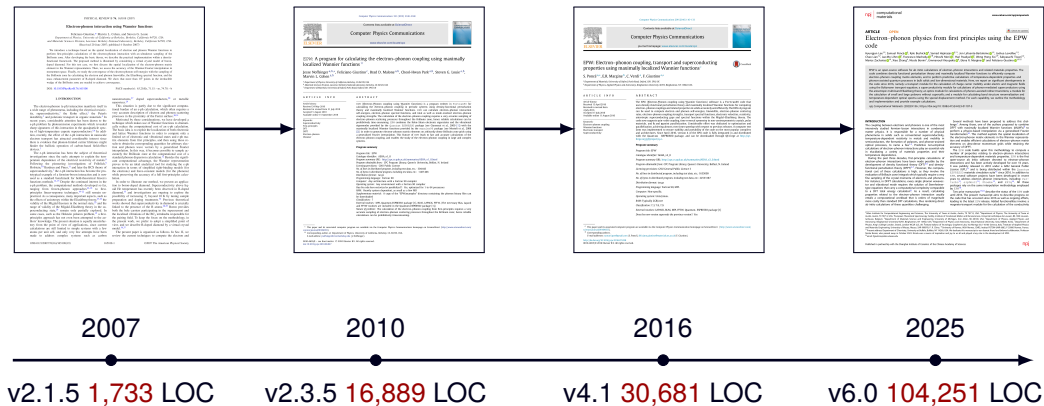
Left figures from: Joe, Kim, et al, Phys. Rev. Lett. 132, 056303 (2024)

Middle figures from: Pack, Dean, et al, Nat. Nanotechnol. 19, 948 (2024)

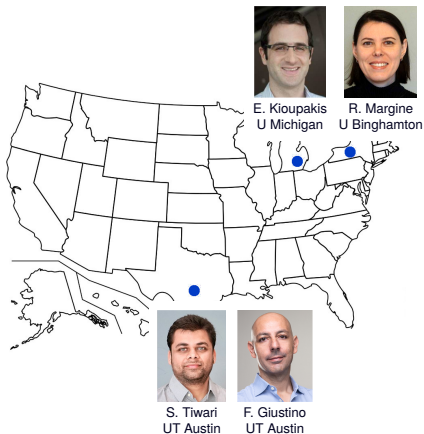
High-throughput screening workflow



The EPW software project



The EPW Collaboration



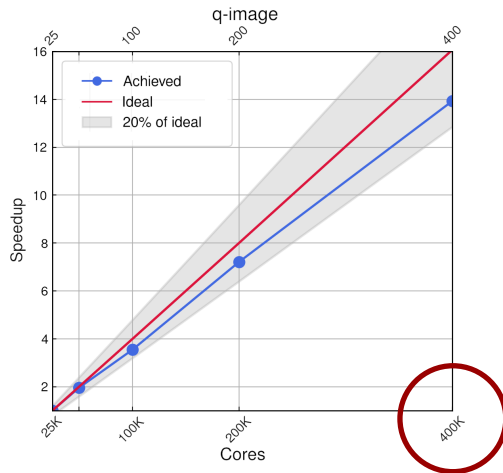
Current developers

Kyle Bushick
Fabio Caruso
Jie-Cheng Chen
Zhenbang Dai
Feliciano Giustino
Viet-Anh Ha
Emmanouil Kioupakis
Jon Lafuente-Bartolomé
Tae Yun Kim
Chao Lian
Jae-Mo Lihm
Zhe Liu
Roxana Margine
Hitoshi Mori
Yiming Pan
Samuel Poncé
Danylo Radevych
Young-Woo Son
Sabyasachi Tiwari
Aidan Thorn
Shashi Mishra
Amanda Wang
Wooil Yang
Marios Zacharias
Xiao Zhang

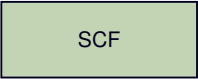
Hybrid MPI/OpenMP in EPW and full-system runs on Frontera



Electron **scattering** rates of MoS₂

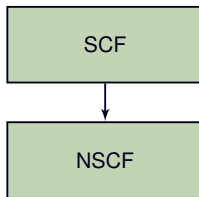


Taming the complexity of advanced calculations

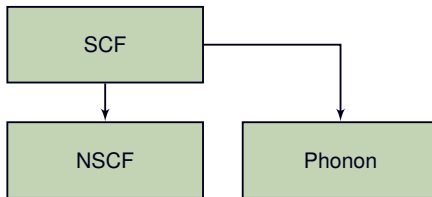


SCF

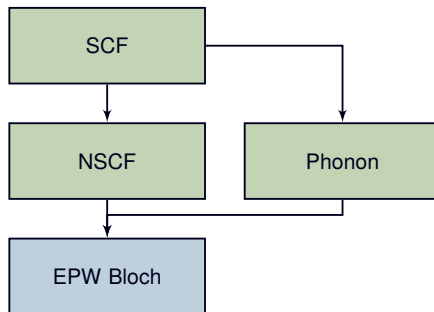
Taming the complexity of advanced calculations



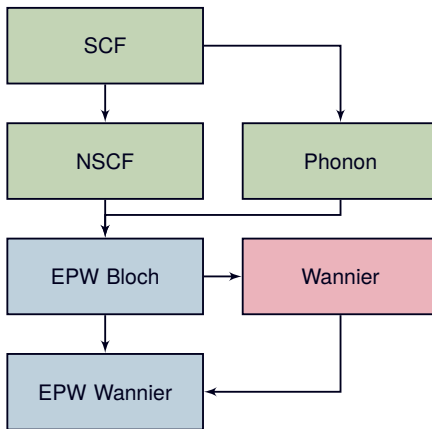
Taming the complexity of advanced calculations



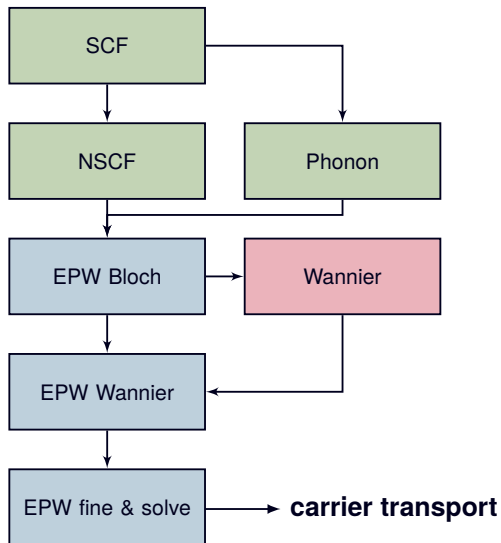
Taming the complexity of advanced calculations



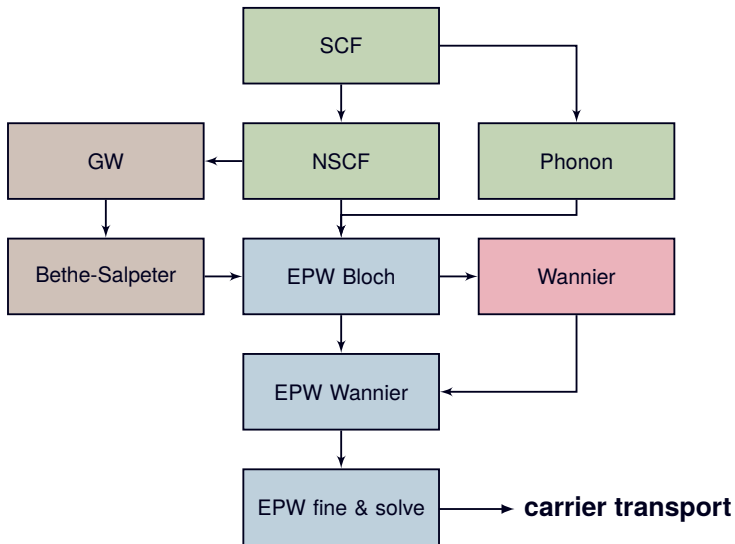
Taming the complexity of advanced calculations



Taming the complexity of advanced calculations



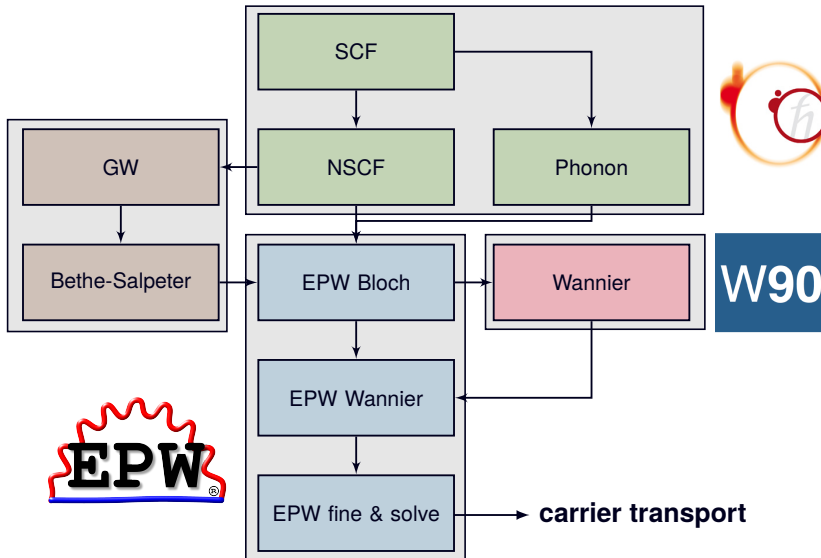
Taming the complexity of advanced calculations



Taming the complexity of advanced calculations



BerkeleyGW



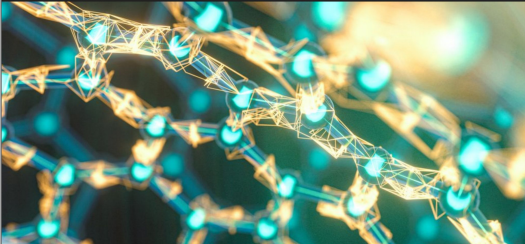
```
silicon = EPWpy({'MatProjID':'mp-149','pseudo_auto':True},code=QE)
silicon.scf(kpoints={'kpoints':[8,8,8]})
```

[illegible]

- Materials are **objects**, properties are **functions**
- Interfaces with
 - Quantum ESPRESSO
 - VASP
 - Abinit
 - BerkeleyGW
 - EPW
- Lightweight
- Intuitive for users and developers

TACC | **TEXAS**

 **MATCSSI** Getting Started About Philosophy Team Codes Help



MATCSSI
Materials Cyberinfrastructure for Sustained Scientific Innovation

A cloud-based portal for intuitive materials modeling using **JupyterHub HPC**



jupyter polaron Last Checkpoint: 11 minutes ago

File Edit View Run Kernel Settings Help

Not Trusted

JupyterLab Python 3 (ipykernel)

EPW workflow for polaron calculations

Set up working environment

Load required modules:

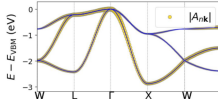
```
[1]: import numpy as np
import scipy.interpolate
import matplotlib.pyplot as plt
from mpl_toolkits.mplot3d import Axes3D
from matplotlib.ticker import MultipleLocator, FormatStrFormatter
import os
import pandas as pd

import sys
print(str(os.getcwd()))
sys.path.insert(0, str(os.getcwd()) + '/../EPWpy/')
from EPWpy import *
from plotting import plot_polaron

/work2/87972/jonl/frantera/Notebooks/matcssi/notebooks_basic
```

[3]: # Plot A_{nk} coefficients

plot_polaron.plot_Ank_Bqvl('Ank', home=prefix+'/path.kpt', sympoints, home=prefix+'/epu/Ank.band.plm')





UT Austin

Viet-Anh Ha
Sabyasachi Tiwari
Tae Yun Kim
Nick Pant
Jie-Cheng Chen
Abu Zubair

Cornell

Grace Xing
Debdeep Jena
Darrell Schlom

USC

Zhenglu Li

KIAS Seoul

Woofil Yang
Young-Woo Son

UC Berkeley

Steven Louie

UCSB

Chris Van de Walle

U Kiel

Yiming Pan
Fabio Caruso

EPW Collaboration

Roxana Margine
Samuel Poncé
Emmanouil Kioupakis
Marios Zacharias
Jon Lafuente-Bartolomé
Chao Lian



U.S. DEPARTMENT OF
ENERGY

Office of
Science

